

## Description

The SUD19P06-60-GE3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **General Features**

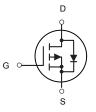
$$\label{eq:VDS} \begin{split} V_{DS} =& -60 V, I_D =& -30 \, A \\ R_{DS(ON)} <& 33 m \Omega @ V_{GS} =& -10 V \end{split}$$

## Application

PWM applications Load switch Power management



### TO-252-2L



P-Channel MOSFET

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SUD19P06-60-GE3	TO-252-2L	HXY MOSFET	2500

## ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage (V <sub>GS</sub> =0V)	-60	V
Vgs	Gate-Source Voltage (V <sub>DS</sub> =0V)	±20	V
1-	Drain Current-Continuous(Tc=25℃)	-30	А
lo	Drain Current-Continuous(Tc=100℃)	-25.5	А
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-144	А
D-	Maximum Power Dissipation(Tc=25 $^\circ\!\!\!{}^\circ\!\!\!{}^\circ\!\!C$ )	79	W
PD	Maximum Power Dissipation(Tc=100 $^\circ\!\!\!\mathrm{C}$ )	39.5	W
Eas	Avalanche energy (Note 2)	196	mJ
Tj, Tstg	Operating Junction and Storage Temperature Range	-55 To 175	°C



P-Channel Enhancement Mode MOSFET

## Electrical Characteristics (TJ=25°C unless otherwise noted)

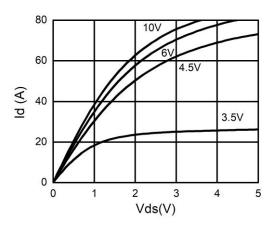
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-60			V
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Igss	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-1	-1.8	-2.5	V
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-15A		35		S
5	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		29	33	mΩ
Rds(on)		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		35	46	mΩ
Ciss	Input Capacitance			4026		pF
Coss	Output Capacitance	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHz		134		pF
Crss	Reverse Transfer Capacitance			98		pF
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V,		12.2		nS
tr	Turn-on Rise Time			10		nS
$t_{d(\text{off})}$	Turn-Off Delay Time	R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		64		nS
t <sub>f</sub>	Turn-Off Fall Time			14		nS
Qg	Total Gate Charge			68		nC
Qgs	Gate-Source Charge	$V_{GS}$ =-10V, $V_{DS}$ =-30V, $I_{D}$ =-20A		10.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			13		nC
Isd	Source-Drain Current (Body Diode)				30	Α
Vsd	Forward on Voltage (Note 3)	Vgs=0V, Is=-15A			-1.2	V
trr	Reverse Recovery Time	I <sub>F</sub> =-20A, di/dt=100A/μs 26		26		ns
Qrr	Reverse Recovery Charge	I⊧=-20A, di/dt=100A/μs		29		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes  $2.E_{AS}$  condition:  $T_J=25^{\circ}C$ ,  $V_{DD}=40V$ ,  $V_G=-10V$ ,  $Rg=25\Omega$ , L=0.5mH. Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



# **Typical Electrical And Thermal Characteristics (Curves)**



## Figure 1. Output Characteristics

#### Figure 3. Power Dissipation

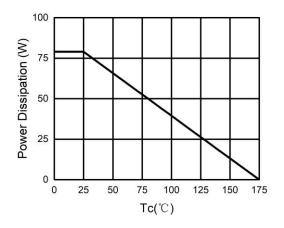


Figure 5. BV<sub>DSS</sub> vs Junction Temperature

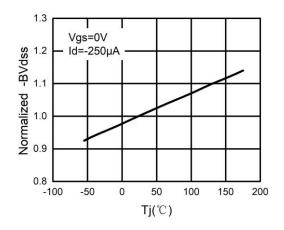


Figure 2. Transfer Characteristics

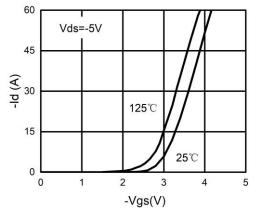


Figure 4. Drain Current

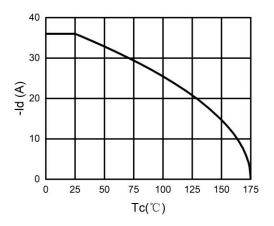
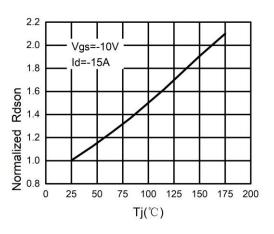
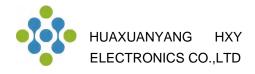
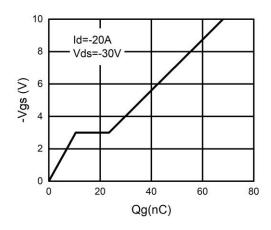


Figure 6. R<sub>DS(ON)</sub> vs Junction Temperature

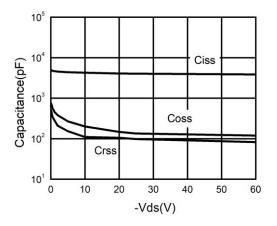






#### Figure 7. Gate Charge Waveforms

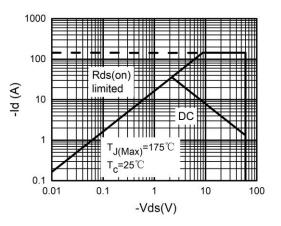
Figure 8. Capacitance

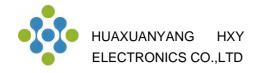


### Figure 9. Body-Diode Characteristics

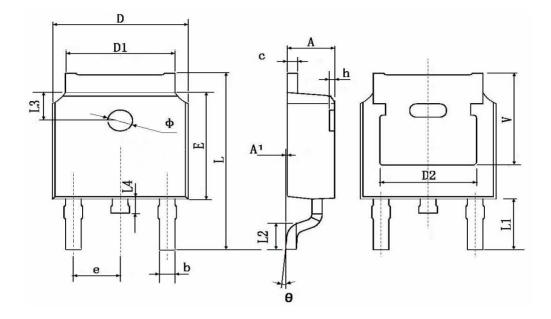
 $(\mathbf{v}_{10}^{-1})_{10^{-1}}$  $(\mathbf{v}_{10^{-1}})_{10^{-1}}$  $10^{-2}$  $10^{-3}$ 0.20.40.60.81.0-Vsd(V)

Figure 10. Maximum Safe Operating Area





# TO-252-2L Package Information



• • •	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
с	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	) TYP.	0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.			3 TYP.		
L4	0.600	1.000	0.024	0.039		
Φ	1.100	1.300	0.043	0.051		
θ	0 °	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	) TYP.	0.211 TYP.			



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